

CURRICULUM VITAE

Name: Dr Mahmoud Gad
Address in Egypt: 2 Abdel Samd street, 10th Min Ramadan street, In front of Ramd Hospital, Kaluob Elmahata, Kaluobia, Egypt.
E-mail : m_gad472003@yahoo.co.uk
Tel.: 00202-42137732 (Egypt)
Mobile: 0020163730387 (Egypt)
Date of birth: 30-09-1966
Nationality: Egyptian
Marital status: Married
Children: Two
Sex: Male

Education

- 1999-2003** **PhD in Physics and Solid State Electronics.**
Department of Electrical Engineering and Electronics, UMIST (The University of Manchester now), Manchester, UK.
Title: “*Optical and Electrical Characterisation of Er-doped Si-based Structures*”
- 1990-1996** **MSc in Physics**
Physics Department, Helwan University, Cairo, Egypt.
Title: “*Interferometric Measurements of Some Optical Parameters for the Fibres*”
- 1989-1990** **Pre-Master courses in optics and laser Physics**
Department of Physics, Helwan University, Cairo, Egypt.
- 1985-1989** **B.Sc. in Physics {grad excellent (%91.65)}**
Physics Department, Helwan University, Cairo-Egypt.
(*First class honour degree for the four years in my undergraduate studies in the physics department*).

Current post

Lecturer in Physics Department, Science Faculty, Helwan University, Cairo, Egypt.

Work experience

In United Kingdom:

- 2004-2007 Post doctoral Research Associate**
Materials and Engineering Research Institute (MERI), Sheffield Hallam University, Sheffield, UK.
EPSRC funded project supervised by Prof Jan Evans-Freeman.
- 2000-2003 Laboratory Demonstrator**
Department of Electrical Engineering and Electronics- UMIST (The University of Manchester now), Manchester, UK.

In Egypt:

- 2005-present Lecturer**
Physics Department, Helwan University, Cairo-Egypt.
I got two years vacation to work as a post doctoral Research Associate in MERI, Sheffield Hallam University, UK.
- 1996-2005 Assistant Lecturer**
Physics department and faculty of engineering, Helwan University, Cairo, Egypt.
I got a vacation from 1999 to 2003 to do my PhD in physics and solid state electronics at department of electrical engineering and electronics, UMIST (The University of Manchester now), Manchester, UK.
- 1990-1996 Demonstrator**
Physics department and faculty of engineering, Helwan University, Cairo, Egypt.

Teaching

Laboratory Section:

- Electronic Circuits and Semiconductor Devices Laboratories for the first and second year undergraduate students.
Department of Electrical Engineering and Electronics, UMIST (The University of Manchester now), Manchester, UK.

- Electricity & magnetism, Heat, properties of matter and Optics Laboratories. Faculties at Helwan University (Science, Engineering, Education and applied art), Cairo, Egypt.

Teaching language: English

Courses:

- Electricity & magnetism, Heat, properties of matter and optics. Faculties at Helwan University, Cairo, Egypt.

Teaching language: English

Training Courses Attended

- Short course in Ion Beam Technology, at Surrey University, Surrey, UK in April 2003.
- Three Months in Semiconductor Devices at Institute of Physics, Polish Academy of Science, Warsaw, Poland in 2004.
- SINANO Modelling Summer School in Gelasgow, Scotland, UK from 15th to 19th August 2005.

Meetings attended

- UK Network on Defects in Silicon and Silicon Germanium, at University of Exeter, UK in 2003
- E-MRS 2003 Spring Meeting, Strasbourg, France.
- UK Network on Defects in Silicon and Silicon Germanium, at Bath University, UK on 3rd May 2002, UK.
- PREP (2002), University of Nottingham, UK.
- Defects in Silicon and Silicon Germanium at Kings College, London, UK on 2nd July 2001.
- Si Workshop on 17th October 2001 at UMIST, Manchester, UK.
- PREP (2001) University of Keele, UK

Publications

1. **M A Gad** and J H Evans-Freeman " *Annealing studies of cluster defects in ion-implanted silicon using high resolution DLTS*" Nuclear Inst. and Methods in Physics Research, B (2006).
2. J H Evans-Freeman, D Emiroglu, **M A Gad**, N Mitromara and K D Vernon-Parry *Deep Electronic States in Ion-Implanted Si*, Invited Paper, Journal Materials Science 41 (2006) 1007-1012.
3. **M A Gad**, J H Evans-Freeman, N Cinosi, and J Sarma " *Loss Measurement of Er-Doped Silicon-On-Insulator Waveguides*" Mater. Sci. Engin. B105 (2003) 79-82.
4. **M A Gad** and J H Evans-Freeman " *High Resolution Minority Carrier Transient Spectroscopy of Si/SiGe/Si Quantum Wells*" Journal of Applied Physics, vol.92, no.9, 1 Nov. 2002, pp.5252-8.
5. **M A Gad** and J H Evans-Freeman " *Single Mode Rib Waveguides Fabrication in Smart Cut[®] Silicon-On-Insulator (SOI) Technology*" Proceedings of PREP 2002, IEE/IOP Conference.
6. J H Evans-Freeman, **M A Gad** " *High resolution minority carrier transient spectroscopy of defects in Si and Si/SiGe quantum wells*" Physica B, **308-310** (2001) 513-516.
7. **M A Gad**, J H Evans-Freeman and J Zhang " *High resolution minority carrier transient spectroscopy of deep levels in SiGe/Si quantum wells*" IEE Digest "Proceedings of PREP2001".
8. **M A Gad** and J H Evans-Freeman " *Annealing behaviour of defect clusters in ion implanted Si*" in preparation for J Appl Phys
9. **M A Gad** and J H Evans-Freeman " *High Resolution Deep Level Transient Spectroscopy of semiconducting diamond*" in preparation for Semicond. Sci Technol.